

RB751CS-40

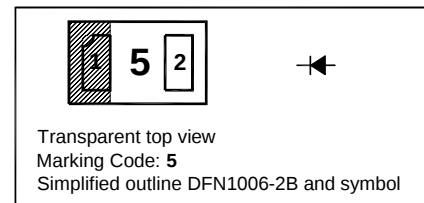
Silicon Epitaxial Planar Schottky Barrier Diode

Features

- Small surface mounting type
- Low forward voltage
- High reliability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

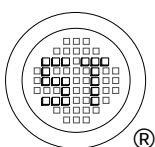
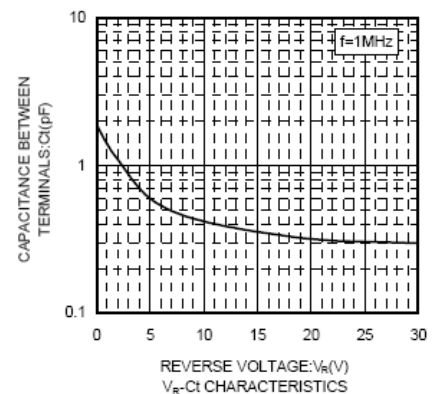
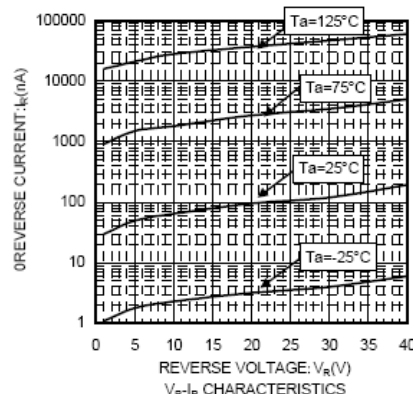
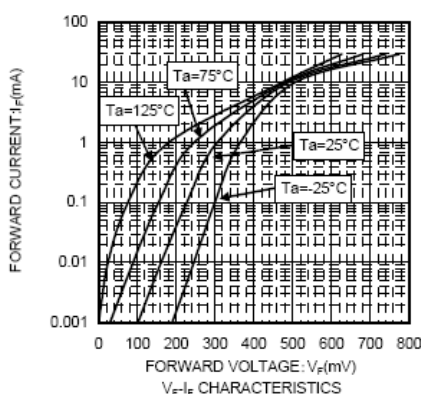


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	30	V
Average rectified forward current	$I_{F(AV)}$	30	mA
Peak Forward Surge Current (60 Hz for 1 Cyc.)	I_{FSM}	200	mA
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$	V_F	-	0.37	V
Reverse Current at $V_R = 30\text{ V}$	I_R	-	0.5	μA
Capacitance Between Terminals at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C_T	2	-	pF



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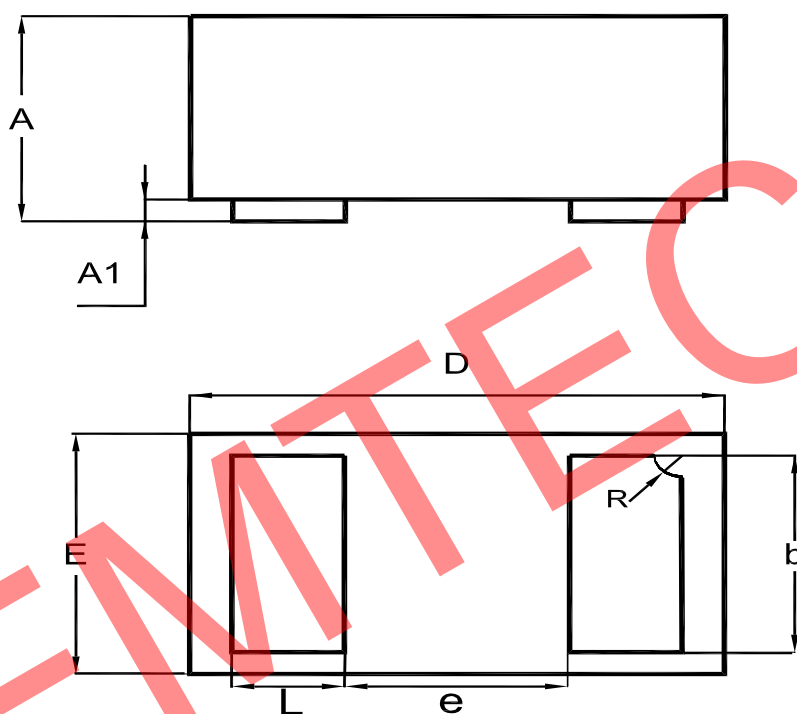


Dated: 02/07/2013 Rev: 02

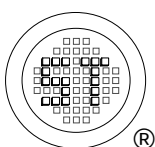
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

DFN1006-2B



UNIT	A	A1	b	D	E	e	L	R
mm	0.41 0.36	0.05 0	0.55 0.45	1.075 0.95	0.675 0.55	0.4	0.3 0.2	0.15 0.05



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